



BAT54CTB

DIODE

SCHOTTKY BARRIER (DUAL) DIODES

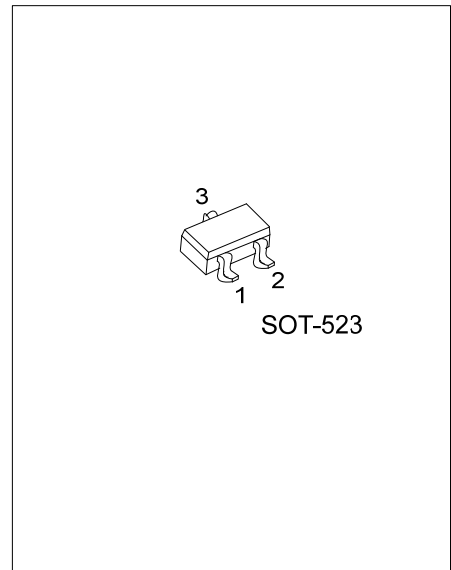
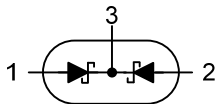
DESCRIPTION

Planar Schottky barrier diodes are encapsulated in the SOT-523 small plastic SMD package. Single diodes and dual diodes with different pin configuration are available.

FEATURES

- * Low forward voltage
- * Guard ring protected
- * Small plastic SMD package

SYMBOL



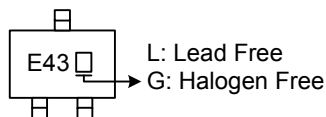
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BAT54CTBL-AN3-R	BAT54CTBG-AN3-R	SOT-523	A1	A2	K1K2	Tape Reel

Note: Pin Assignment: A: Anode K: Cathode

<p>BAT54CTBG-AN3-R</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) R: Tape Reel (2) AN3: SOT-523 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified.)

PARAMETER	SYMBOL	RATINGS	UNIT
Per diode			
Continuous Reverse Voltage	V_R	30	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current ($t_P < 1\text{s}$, $\delta \leq 0.5$)	I_{FRM}	300	mA
Non-repetitive Peak Forward Current ($t_P < 10\text{ms}$)	I_{FSM}	600	mA
Junction Temperature	T_J	+125	$^\circ\text{C}$
Storage Temperature	T_{STG}	-60 ~ +150	$^\circ\text{C}$
Per device			
Power Dissipation ($T_A \leq 25^\circ\text{C}$)	P_D	230	mW

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	500	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage (See Fig.1)	V_F	$I_F = 0.1\text{mA}$			240	mV
		$I_F = 1\text{mA}$			320	mV
		$I_F = 10\text{mA}$			400	mV
		$I_F = 30\text{mA}$			500	mV
		$I_F = 100\text{mA}$			800	mV
Reverse Current (See Fig.2)	I_R	$V_R = 25\text{V}$			2	μA
Reverse Recovery Time (see Fig.4)	t_{rr}	When switched from $I_F = 10\text{mA}$ to $I_R = 10\text{mA}$, $R_L = 100\Omega$ measured at $I_R = 1\text{mA}$			5	ns
Diode Capacitance (see Fig.3)	C_D	$f = 1\text{MHz}$, $V_R = 1\text{V}$;			10	pF

TYPICAL CHARACTERISTICS

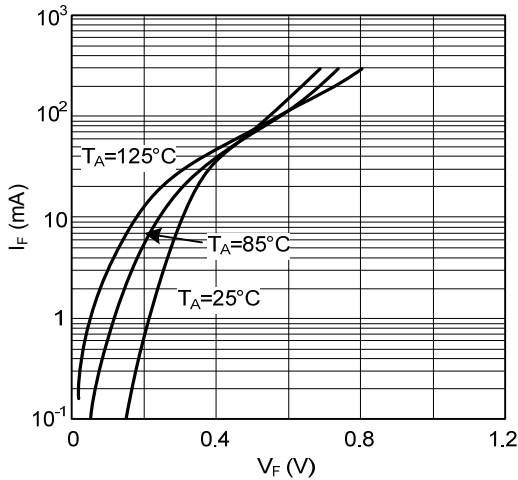


Fig.1 Forward current as a function of forward voltage; typical values.

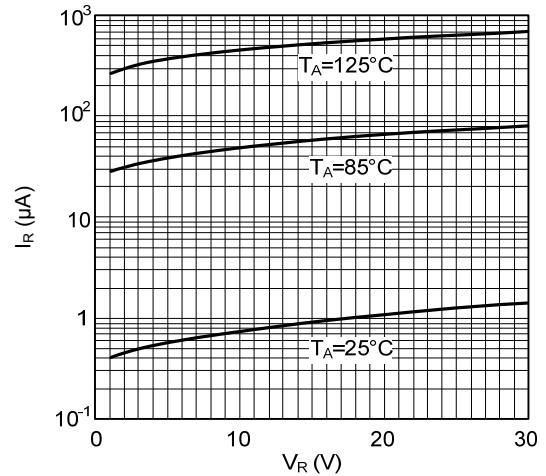


Fig.2 Reverse current as a function of reverse voltage; typical values.

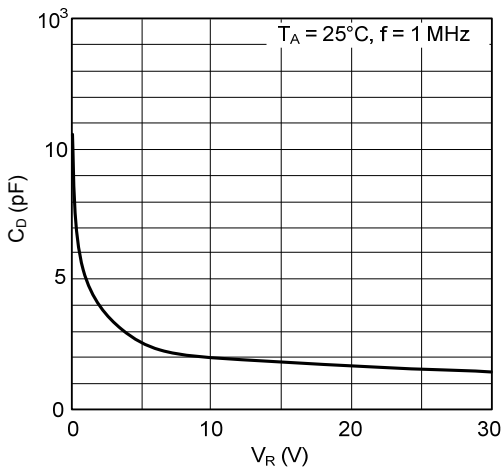


Fig.3 Diode capacitance as a function of reverse voltage; typical values.

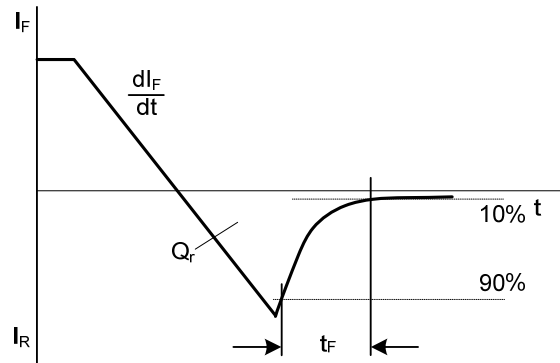


Fig.4 Reverse recovery definitions

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